

STARPOWER

SEMICONDUCTOR

IGBT

GD600HFY120C2S

1200V/600A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

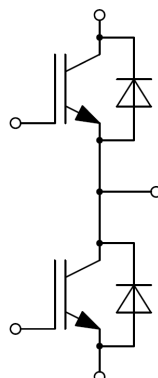
- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using HPS DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=100^{\circ}\text{C}$	1000 600	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	3409	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.65	2.10	V
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.95		
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=24.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.3	5.8	6.3	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			1.3		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		39.4		nF
C_{res}	Reverse Transfer Capacitance			2.14		nF
Q_G	Gate Charge	$V_{GE}=-15 \dots +15\text{V}$		4.62		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		257		ns
t_r	Rise Time			96		ns
$t_{d(off)}$	Turn-Off Delay Time			628		ns
t_f	Fall Time			103		ns
E_{on}	Turn-On Switching Loss			37.5		mJ
E_{off}	Turn-Off Switching Loss			51.5		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		268		ns
t_r	Rise Time			107		ns
$t_{d(off)}$	Turn-Off Delay Time			659		ns
t_f	Fall Time			144		ns
E_{on}	Turn-On Switching Loss			53.5		mJ
E_{off}	Turn-Off Switching Loss			77.3		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		278		ns
t_r	Rise Time			118		ns
$t_{d(off)}$	Turn-Off Delay Time			680		ns
t_f	Fall Time			155		ns
E_{on}	Turn-On Switching Loss			58.9		mJ
E_{off}	Turn-Off Switching Loss			82.4		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		2400		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.65	2.10	V
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		1.65		
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		1.65		
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=25^{\circ}\text{C}$		61.4		μC
I_{RM}	Peak Reverse Recovery Current			280		A
E_{rec}	Reverse Recovery Energy			20.9		mJ
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=125^{\circ}\text{C}$		114		μC
I_{RM}	Peak Reverse Recovery Current			415		A
E_{rec}	Reverse Recovery Energy			43.1		mJ
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=150^{\circ}\text{C}$		128		μC
I_{RM}	Peak Reverse Recovery Current			443		A
E_{rec}	Reverse Recovery Energy			50.0		mJ

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.044	K/W
	Junction-to-Case (per Diode)			0.078	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.109		K/W
	Case-to-Heatsink (per Diode)		0.194		
	Case-to-Heatsink (per Module)		0.035		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

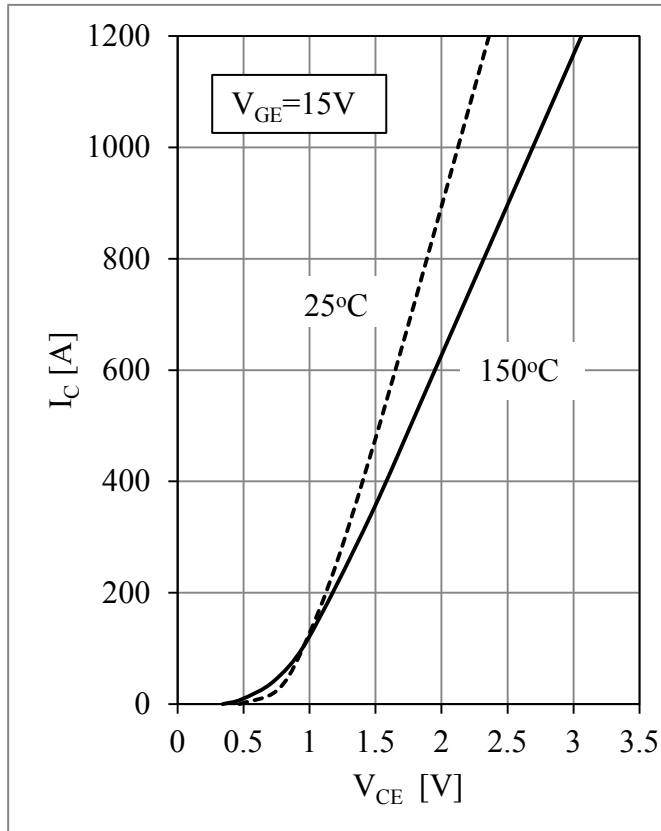


Fig 1. IGBT Output Characteristics

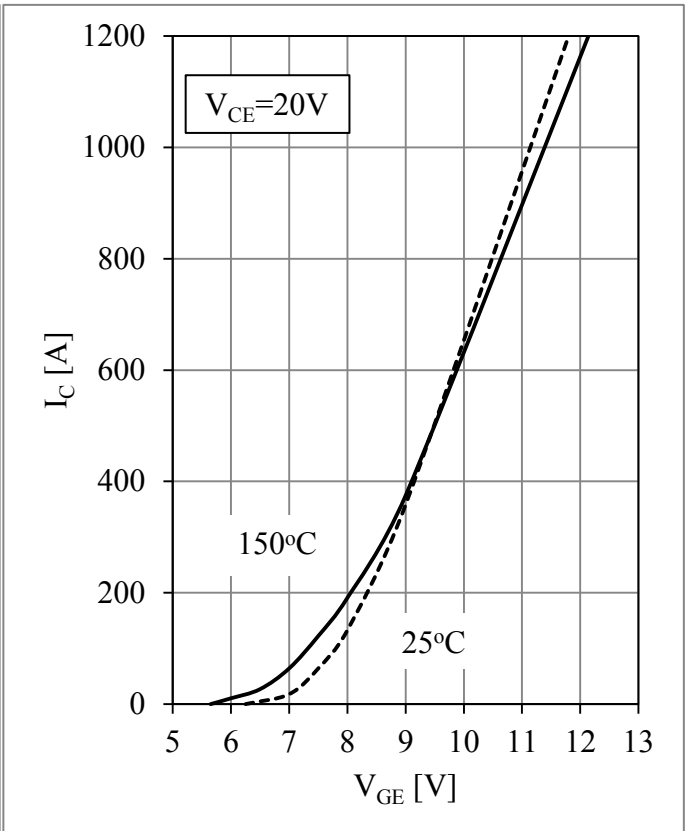
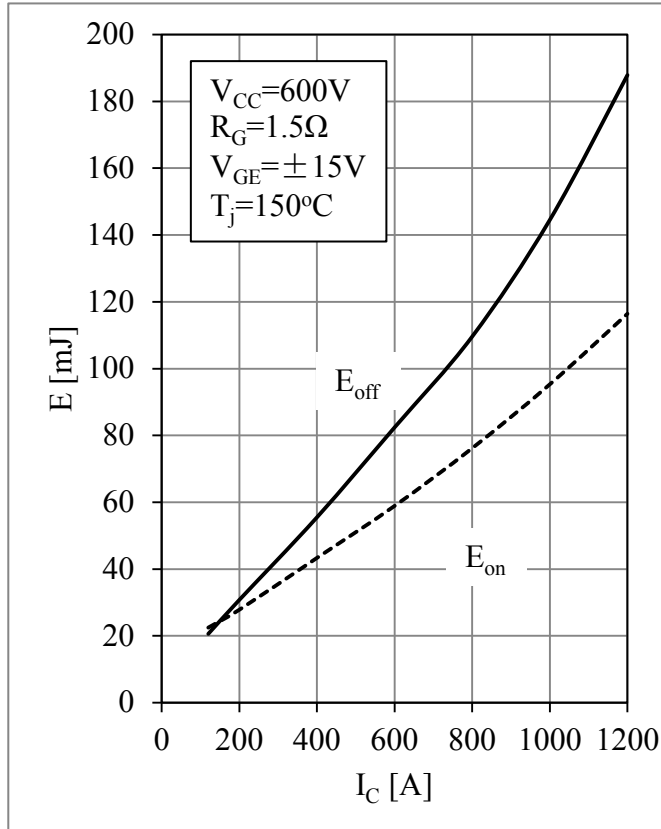
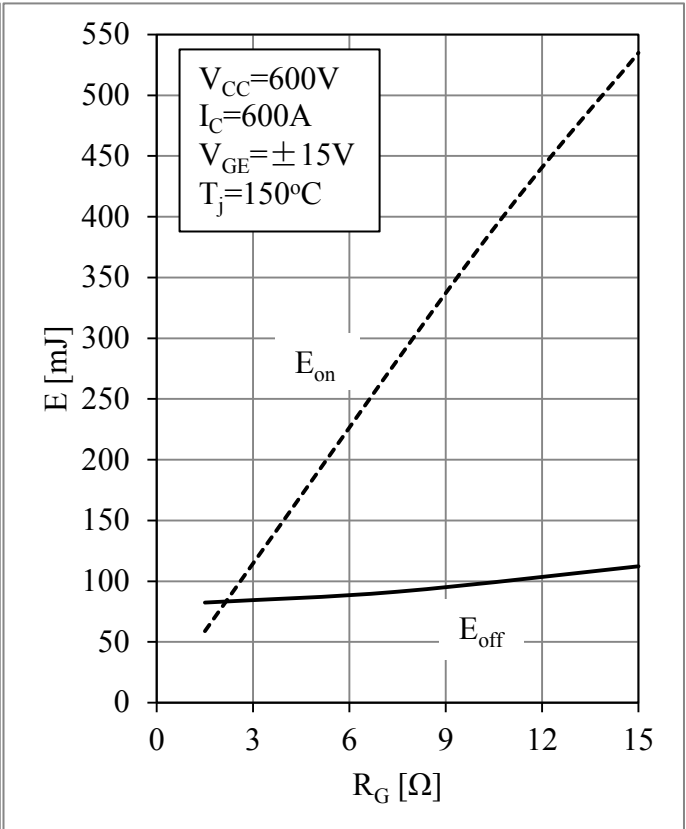


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

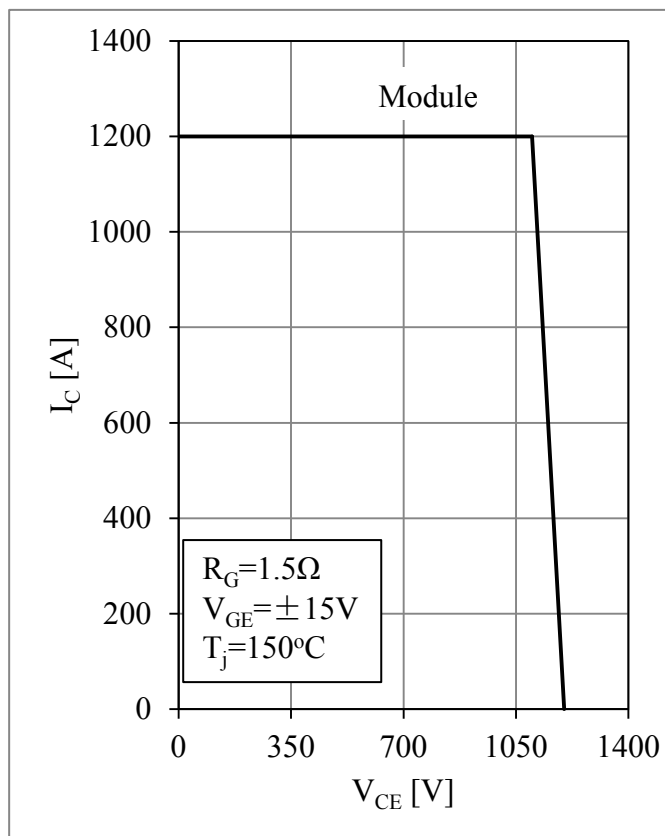


Fig 5. RBSOA

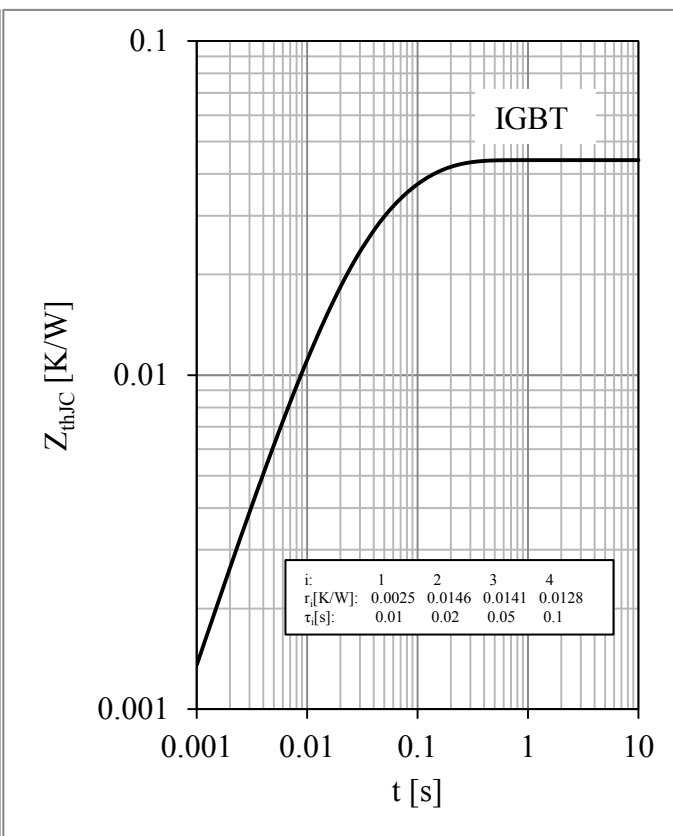


Fig 6. IGBT Transient Thermal Impedance

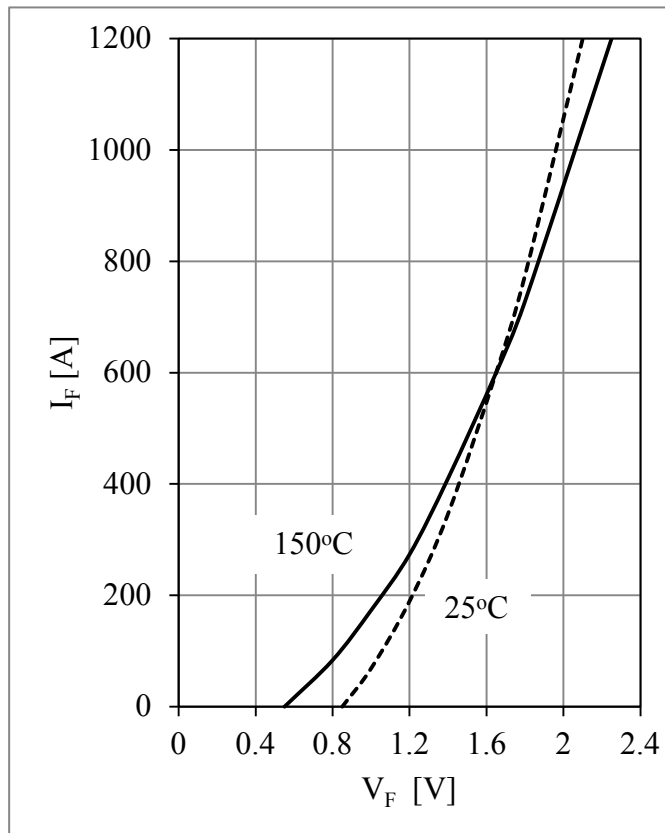
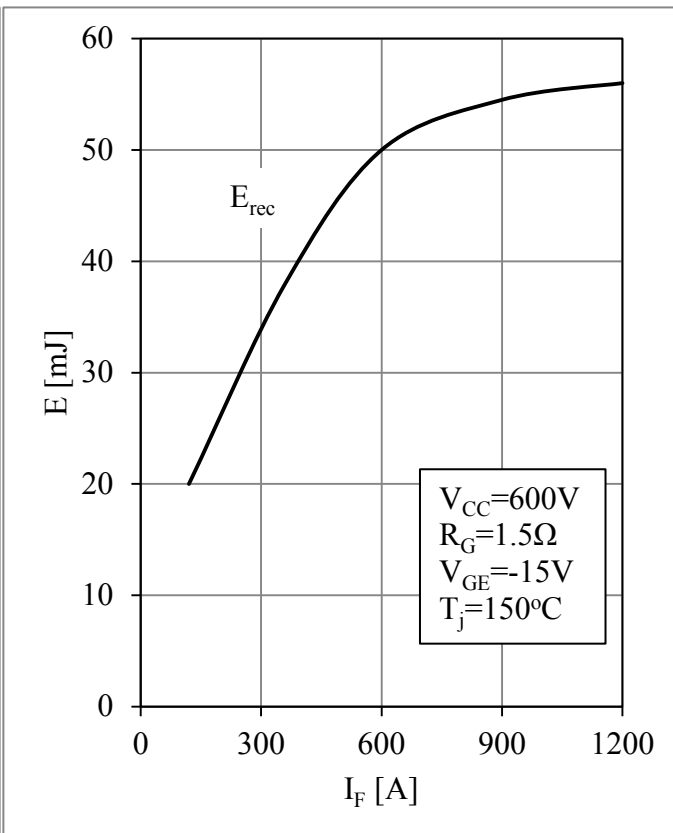


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

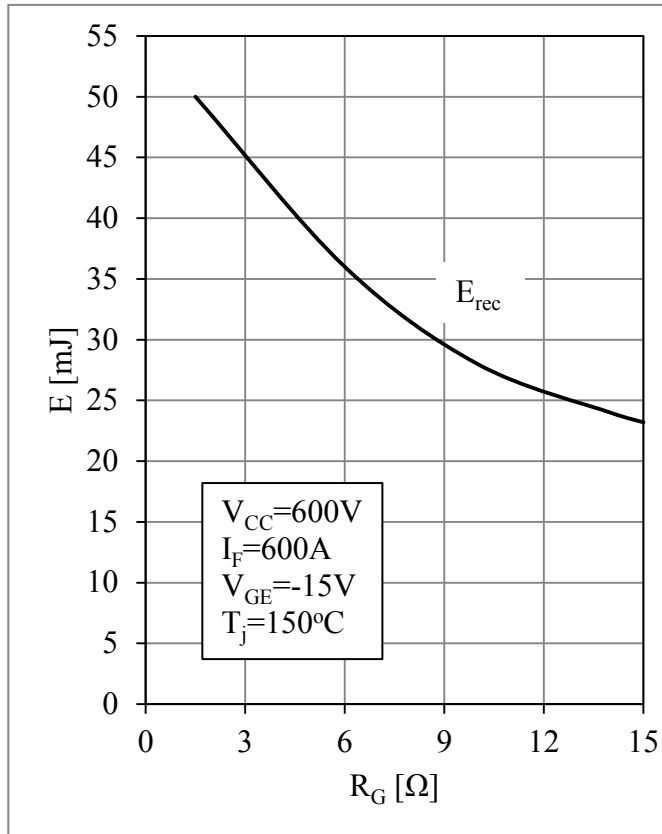
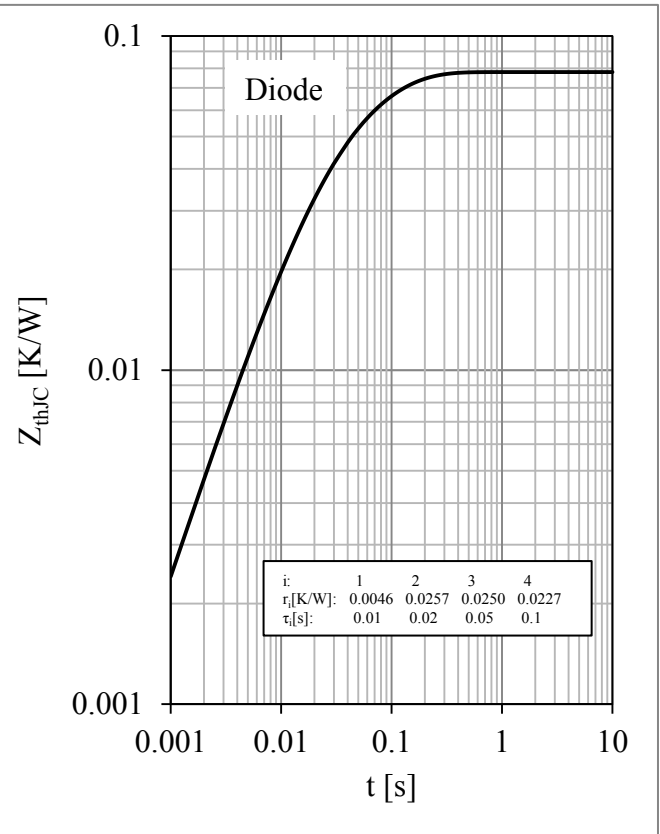
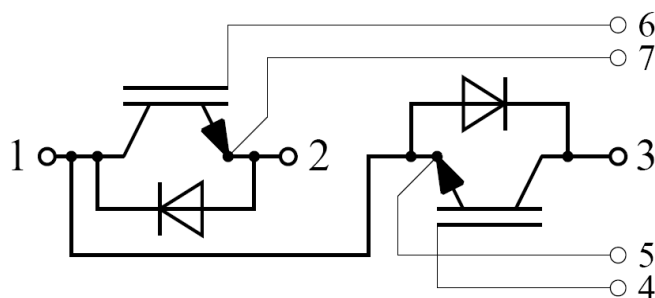
Fig 9. Diode Switching Loss vs. R_G 

Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters

